



FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICESUPPLEMENTAL INFORMATION DISCLOSURE
STATEMENT BY APPLICANTATTY. DOCKET NO.
ELM/002 Div. 6APPLN. NO.
10/614,067APPLICANTS
Glenn J. LeedyCONF. NO.
8117FILING DATE
July 3, 2003GROUP ART UNIT
2812

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
REP	4,500,905	02/19/1985	Shibata	357	68	
REP	4,939,568	07/03/1990	Kato, et al.	357	75	
REP	4,892,753	01/09/1990	Wang, et al.	427	579	
REP	5,000,113	03/19/1991	Wang, et al.	118	723	
REP	5,240,458	08/31/1993	Linglain, et al.	464	63	
REP	5,259,247	11/09/1993	Bantien	73	718	
	RE 34,893	04/04/1995	Fujii, et al.	257	419	
	RE 36,623	03/21/2000	Wang, et al.	427	579	
REP	6,087,284	07/11/2000	Brix, et al.	501	69	
REP	6,518,073	02/11/2003	Momohara	438	4	12/10/2001

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
REP	04-196,263	07/1992	Japan				

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL	
REP	Aboaf, J.A., "Stresses in SiO ₂ Films Obtained from the Thermal Decomposition of Tetraethylorthosilicate - Effect of Heat Treatment and Humidity," J. Electrochem. Soc.: Solid State Science; 116(12): 1732-1736 (Dec. 1969).
REP	Scheuerman, R.J., "Fabrication of Thin Dielectric Films with Low Internal Stresses," J. Vac. Sci. and Tech., 7(1): 143-146 (1970).
REP	Bailey, R., "Glass for Solid-State Devices: Glass film has low intrinsic compressive stress for isolating active layers of magnetic-bubble and other solid-state devices," NASA Tech Brief (1982).
REP	"Partitioning Function and Packaging of Integrated Circuits for Physical Security of Data," IBM Technical Disclosure Bulletin, IBM Corp.; 32(1): 46-49 (June 1989).
REP	Hsieh, et al., "Directional Deposition of Dielectric Silicon Oxide by Plasma Enhanced TEOS Process," 1989 Proceedings, Sixth International IEEE VLSI Multilevel Interconnection Conference, pp. 411-415 (1989).
REP	Tessier, et al., "An Overview of Dielectric Materials for Multichip Modules," SPE, Electrical & Electronic Div.; (6): 260-269 (1991).






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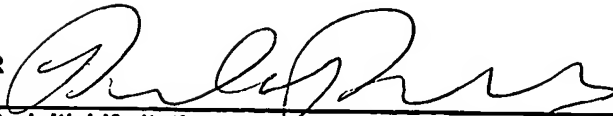
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	APPLICANTS Glenn J. Leedy	CONF. NO. 8117
	FILING DATE July 3, 2003	GROUP ART UNIT 2812

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EXAMINER INITIAL	
	Treichel, et al., "Planarized Low-Stress Oxide/Nitride Passivation for ULSI Devices," J. Phys IV, Colloq. (France), 1 (C2): 839-846 (1991).
	Krishnamoorthy, et al., "3-D Integration of MQW Modulators Over Active Submicron CMOS Circuits: 375 Mb/s Transimpedance Receiver -Transmitter Circuit," IEEE Photonics Technology Letters, 2(11): 1288-1290 (November 1995).
	Tielert, et al., "Benefits of Vertically Stacked Integrated Circuits for Sequential Logic," IEEE, XP-000704550, 121-124 (December 5, 1996).
	"Miniature Electron Microscopes Without Vacuum Pumps, Self-Contained, Microfabricated Devices with Short Working Distances, Enable Operation in Air," NASA Tech Briefs, 39-40 (1998).
	Partial European Search Report for Application No. EP 02009643 (October 8, 2002).

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EXAMINE R INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
<i>JEP</i>	Re. 34,893	04/04/95	Fujii et al.	257	419	
	2,915,722	12/01/59	Foster	336	115	
	3,202,948	08/24/65	Farrand	336	115	
	3,559,282	02/02/71	Lesk	438	113	
	3,560,364	02/02/71	Burkhardt	324	207.12	
	3,602,982	09/07/71	Emmasingel	29	577	
	3,615,901	10/26/71	Medicus	148	11.5 R	
	3,716,429	02/13/73	Napoli et al.	156	17	
	3,777,227	12/14/73	Krishna et al.	257	578	
	3,868,565	02/25/75	Kuipers	324	207.26	
	3,922,705	11/25/75	Yerman	357	26	
	3,997,381	12/14/76	Wanlass	156	3	
	4,070,230	01/24/78	Stein	156	657	
	4,131,985	01/02/79	Greenwood et al.	29	580	
	4,142,004	02/27/79	Hauser, Jr. et al.	438	792	
	4,251,909	02/24/81	Hoeberechts	29	580	
	4,262,631	04/21/81	Kubacki	118	723MP	
	4,394,401	07/19/83	Shioya et al.	427	574	
	4,401,986	08/30/83	Trenkler et al.	340	870.32	
	4,416,054	11/22/83	Thomas et al.	29	572	
	4,539,068	09/03/85	Takagi et al.	156	614	
	4,585,991	04/29/86	Reid et al.	324	158 P	
	4,612,083	09/16/86	Yasumoto et al.	156	633	
	4,617,160	10/14/86	Belanger et al.	264	40.1	
	4,618,397	10/21/86	Shimizu et al.	156	628	
	4,618,763	10/21/86	Schmitz	250	211R	
	4,663,559	05/05/87	Christensen	313	336	
	4,684,436	08/04/87	Burns et al.	216	65	
<i>JEP</i>	4,693,770	09/15/87	Hatada	156	151	

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
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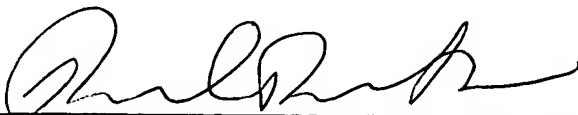
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	4,702,336	10/27/87	Maeda et al.	180	197	
	4,702,936	10/27/87	Seibert et al.	427	583	
	4,706,166	11/10/87	Go	361	403	
	4,721,938	01/26/88	Stevenson	338	4	
	4,761,681	08/02/88	Reid	357	68	
	4,784,721	11/15/88	Holmen et al.	156	647	
	4,810,673	03/07/89	Freeman	438	386	
	4,825,277	04/25/89	Mattox et al.	257	639	
	4,857,481	08/15/89	Tam et al.	438	619	
	4,924,589	05/15/90	Leedy	438	6	
	4,940,916	07/10/90	Borel et al.	313	306	
	Re B14,940,916	11/26/96	Borel et al.	315	306	
	4,950,987	08/21/90	Vranish et al.	324	207.23	
	4,952,446	08/18/90	Lee et al.	428	220	
	4,954,865	09/04/90	Rokos	257	378	
	4,957,882	09/18/90	Shinomiya	438	65	
	4,965,415	10/23/90	Young et al.	200	83 N	
	4,966,663	10/30/90	Mauger	205	656	
	4,994,735	02/19/91	Leedy	324	158	
	5,008,619	04/16/91	Keogh et al.	324	207.17	
	5,010,024	04/23/91	Allen et al.	438	659	
	5,020,219	06/04/91	Leedy	29	846	
	5,034,685	07/23/91	Leedy	324	158 F	
	5,070,026	12/03/91	Greenwald et al.	437	3	
	5,071,510	12/10/91	Findler et al.	156	647	
	5,098,865	03/24/92	Machado et al.	438	788	
	5,103,557	04/14/92	Leedy	29	832	
	5,110,373	05/05/92	Mauger	148	33.2	
	5,111,278	05/05/92	Eichelberger	357	75	
	5,116,777	05/26/92	Chan et al.	438	234	
	5,130,894	07/14/92	Miller	361	393	
	5,132,244	07/21/92	Roy	438	477	

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<i>REP</i>	5,151,775	09/29/92	Hadwin	357	80	
	5,156,909	10/20/92	Henager, Jr. et al.	428	334	
	5,203,731	04/20/93	Zimmerman	445	24	
	5,225,771	07/06/93	Leedy	324	158	
	5,236,118	08/17/93	Bower et al.	228	193	
	5,262,351	11/16/93	Bureau et al.	437	183	
	5,270,261	12/14/93	Bertin et al.	437	209	
	5,273,940	12/28/93	Sanders	437	209	
	5,274,270	12/28/93	Tuckerman	257	758	
	5,279,865	01/18/94	Chebi et al.	427	574	
	5,284,796	02/08/94	Nakanishi et al.	437	183	
	5,323,035	06/21/94	Leedy	257	48	
	5,324,687	06/28/94	Wojnarowski	437	225	
	5,354,695	10/11/94	Leedy	438	411	
	5,363,021	11/08/94	MacDonald	315	366	
	5,385,909	01/31/95	Nelson et al.	514	291	
	5,385,632	01/31/95	Goossen	156	630	
	5,420,458	05/30/95	Shimoji	257	622	
	5,424,920	06/13/95	Miyake	361	735	
	5,426,072	06/20/95	Finnila	437	208	
	5,426,363	06/20/95	Akagi et al.	324	239	
	5,432,444	07/11/95	Yasohama et al.	324	240	
	5,432,729	07/11/95	Carson et al.	365	63	
	5,434,500	07/18/95	Hauck et al.	324	67	
	5,451,489	09/19/95	Leedy	430	313	
	5,453,404	09/26/95	Leedy	437	203	
	5,457,879	10/17/95	Gurtler et al.	29	895	
	5,476,813	12/19/95	Naruse	437	132	
	5,489,554	02/06/96	Gates	437	208	
	5,502,667	03/26/96	Bertin et al.	365	51	
<i>REP</i>	5,512,397	04/30/96	Leedy	430	30	
	5,527,645	06/18/96	Pati et al.	430	5	

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
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	5,529,829	06/25/96	Koskenmaki et al.	428	167	
	5,534,465	07/09/96	Frye et al.	437	209	
	5,555,212	09/10/96	Toshiaki et al.	365	200	
	5,563,084	10/08/96	Ramm et al.	437	51	
	5,571,741	11/05/96	Leedy	437	51	
	5,580,687	12/03/96	Leedy	430	5	
	5,581,498	12/03/96	Ludwig et al.	365	63	
	5,582,939	12/10/96	Pierrat	430	5	
	5,583,688	12/10/96	Hornbeck	359	291	
	5,592,007	01/07/97	Leedy	257	347	
	5,592,018	01/07/97	Leedy	257	619	
	5,595,933	01/21/97	Heijboer	439	20	
	5,606,186	02/25/97	Noda	257	226	
	5,627,112	05/06/97	Tennant et al.	438	113	
	5,629,137	05/13/97	Leedy	430	313	
	5,633,209	05/27/97	Leedy	435	228	
	5,637,536	06/10/97	Val	438	686	
	5,654,127	08/05/97	Leedy	430	315	
	5,654,220	08/05/97	Leedy	438	25	
	5,656,552	08/12/97	Hudak et al.	438	15	
	5,675,185	10/07/97	Chen et al.	257	774	
	5,694,588	12/02/97	Ohara et al.	395	566	
	5,725,995	03/10/98	Leedy	430	315	
	5,750,211	05/12/98	Weise et al.	427	579	
	5,760,478	06/02/98	Bozso et al.	257	777	
	5,773,152	06/30/98	Okonogi	428	446	
	5,786,116	07/28/98	Rolfson	430	5	
	5,793,115	08/11/98	Zavracky et al.	257	777	
	5,831,280	11/03/98	Ray	257	48	
	5,834,334	11/10/98	Leedy	438	107	
	5,840,593	11/24/98	Leedy	438	6	
	5,856,695	01/05/99	Ito et al.	257	370	

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722	5,868,949	02/09/99	Sotokawa et al.	216	18	
	5,869,354	02/09/99	Leedy	438	110	
	5,870,176	02/09/99	Sweatt et al.	355	53	
	5,880,010	03/09/99	Davidson	438	455	
	5,882,532	03/16/99	Field et al.	216	2	
	5,902,118	05/11/99	Hübner	438	106	
	5,915,167	06/22/99	Leedy	438	108	
	5,946,559	08/31/99	Leedy	438	157	
	5,985,693	11/16/99	Leedy	438	107	
	5,998,069	12/07/99	Cutter et al.	430	5	
	6,008,126	12/28/99	Leedy	438	667	
	6,020,257	02/01/00	Leedy	438	626	
	6,045,625	04/04/00	Houston	148	33.3	
	6,084,284	07/04/00	Adamic, Jr.	257	506	
	6,097,096	08/01/00	Gardner et al.	257	777	
	6,133,640	10/17/00	Leedy	257	778	
	6,194,245 B1	02/27/01	Tayanaka	438	57	
	6,197,456 B1	03/06/01	Aleshin et al.	430	5	
	6,208,545 B1	03/27/01	Leedy	365	51	
	6,236,602 B1	05/22/01	Patti	365	201	
	6,261,728 B1	07/17/01	Lin	430	30	
	6,288,561 B1	09/11/01	Leedy	324	760	
720	6,294,909 B1	09/25/01	Leedy	324	207.17	

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO
722	WO 98/19337	05/1998	PCT	H01L	21/44		
722	GB 2,215,168	09/1989	UK	G09G	1/00		
722	EP 0 189 976	08/1986	EPO	H01L	31/18		
722	EP 0 731 525	09/1996	EPO	H01P	5/00		
722	2641129	12/1988	France	H01L	39/04		
722	JP 60-74643	04/1985	Japan			ABST	

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REP	JP 02-082564	03/1990	Japan			ABST	
REP	JP 04-083371	03/1992	Japan			ABST	
REP	JP 04-107964	04/1992	Japan			ABST	
REP	JP 402027600A	01/1990	Japan			ABST	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

EXAMINER INITIAL	
REP	"IC Tower Patent: Simple Technology Receives Patent on the IC Tower, a Stacked Memory Technology," http://www.simpletech.com/whatsnew/memory/@60824.htm (1998).
REP	Alloert, K., et al., "A Comparison Between Silicon Nitride Films Made by PCVD of N ₂ -SiH ₄ /Ar and N ₂ -SiH ₄ /He," <i>Journal of the Electrochemical Society</i> , Vol. 132, No. 7, pp. 1763-1766, (July 1985).
REP	Hendricks, et al., "Polyquinoline Coatings and Films: Improved Organic Dielectrics for IC's and MCM's," <i>Eleventh IEEE/CHMT International Electronics Manufacturing Technology Symposium</i> , pp. 361-265 (1991).
REP	Knolle, W.R., et al., "Characterization of Oxygen-Doped, Plasma-Deposited Silicon Nitride," <i>Journal of the Electrochemical Society</i> , Vol. 135, No. 5, pp. 1211-1217, (May 1988).
REP	Nguyen, S.V., "Plasma Assisted Chemical Vapor Deposited Thin Films for Microelectronic Applications, <i>J. Vac. Sci. Technol.</i> Vol. B4, No. 5, pp.1159-1167, (Sep/Oct. 1986).
REP	Olmer, et al., "Intermetal Dielectric Deposition by Plasma Enhanced Chemical Vapor Deposition," <i>Fifth IEEE/CHMT International Electronic Manufacturing Technology Symposium - Design-to-Manufacturing Transfer Cycle</i> , pp. 98-99 (1988).
REP	Runyan, W.R., "Deposition of Inorganic Thin Films," <i>Semiconductor Integrated Circuit Processing Technology</i> , p. 142 (1990).
REP	Sze, S.M., "Surface Micromachining," <i>Semiconductor Sensors</i> , pp. 58-63 (1994).
REP	Vossen, John L., "Plasma-Enhanced Chemical Vapor Deposition," <i>Thin Film Processes II</i> , pp. 536-541 (1991).
REP	Wolf, Stanley, "Basics of Thin Films," <i>Silicon Processing for the VLSI Era</i> , pp. 115, 192, 193, and 199 (1986).

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